



#29/C
Dking
12.30.02

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q54431

Toshiro HAYAKAWA, et al.

Application No.: 09/315,068

Group Art Unit: 2828

Confirmation No.: 5982

Examiner: Jeffrey N. Zahn

Filed: May 20, 1999

RECEIVED
DEC 23 2002
TECHNOLOGY CENTER 2800

For: SEMICONDUCTOR LASER AND METHOD OF MANUFACTURING THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated August 29, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

2. (Amended) A semiconductor laser as defined in Claim 1 in which the structure where said part of the upper cladding layer on the upper optical waveguide layer which is selectively removed up to the interface of the upper cladding layer and the upper optical waveguide layer forms a ridge structure.

7. (Amended) A semiconductor laser as defined in Claim 6, wherein a thickness of the upper cladding layer is greater than zero, but less than 1 μ m.

37 CFR 1.30